

DZ2J068×0L

Silicon epitaxial planar type

For constant voltage / For surge absorption circuit

■ Features

- Excellent rising characteristics of zener current I_Z
- Low zener operating resistance R_Z
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: GJ or GU

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive peak forward current	IFRM	200	mA
Total power dissipation ^{*1}	PT	200	mW
Electrostatic discharge ^{*2}	ESD	±15	kV
Junction temperature	Tj	150	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +150	°C

Note) *1 Mounted on glass epoxy print board (45 mm × 45 mm × 1 mm)

Solder in (Recommended land pattern)

*2 Test method : IEC61000_4_2

(C = 150 pF, R = 330 Ω, Contact discharge : 10 times)

■ Electrical Characteristics $T_a = 25\text{ }^\circ\text{C} \pm 3\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	VF	IF = 10 mA			1.0	V
Zener voltage ^{*1, *2}	VZ	IZ = 5 mA	6.46		7.14	V
Zener operating resistance	RZ	IZ = 5 mA			20	Ω
Zener rise operating resistance	RZK	IZ = 0.5 mA			60	Ω
Reverse current	IR	VR = 4 V			0.1	μA
Temperature coefficient of zener voltage ^{*3}	SZ	IZ = 5 mA		3.2		mV/°C

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.

2. Absolute frequency of input and output is 5 MHz.

3. *1 The temperature must be controlled 25 °C for VZ measurement.

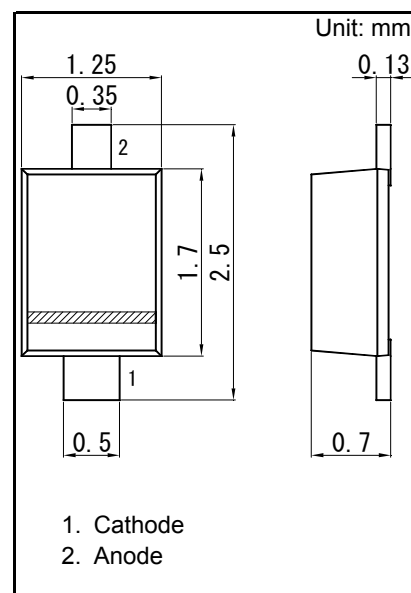
VZ value measured at other temperature must be adjusted to VZ (25 °C).

*2 VZ guaranteed 20 ms after current flow

*3 Tj = 25 °C to 150 °C

Rank classification

Code	M	0
Rank	M	No-rank
VZ	6.64 to 6.98	6.46 to 7.14
Marking symbol	GJ	GJ



1. Cathode
2. Anode

Panasonic	SMini2-F5-B
JEITA	SC-90A
Code	—

Internal Connection

